

M Pepper

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/11984704/publications.pdf>

Version: 2024-02-01

615
papers

26,092
citations

14655

66
h-index

8866

145
g-index

618
all docs

618
docs citations

618
times ranked

10984
citing authors

#	ARTICLE	IF	CITATIONS
1	New Method for High-Accuracy Determination of the Fine-Structure Constant Based on Quantized Hall Resistance. Physical Review Letters, 1980, 45, 494-497.	7.8	5,601
2	One-dimensional transport and the quantisation of the ballistic resistance. Journal of Physics C: Solid State Physics, 1988, 21, L209-L214.	1.5	1,885
3	Possible Spin Polarization in a One-Dimensional Electron Gas. Physical Review Letters, 1996, 77, 135-138.	7.8	657
4	One-Dimensional Conduction in the 2D Electron Gas of a GaAs-AlGaAs Heterojunction. Physical Review Letters, 1986, 56, 1198-1201.	7.8	594
5	Measurements of Coulomb blockade with a noninvasive voltage probe. Physical Review Letters, 1993, 70, 1311-1314.	7.8	535
6	<i>In vivo</i> study of human skin using pulsed terahertz radiation. Physics in Medicine and Biology, 2004, 49, 1595-1607.	3.0	430
7	Terahertz Frequency Sensing and Imaging: A Time of Reckoning Future Applications?. Proceedings of the IEEE, 2005, 93, 1722-1743.	21.3	370
8	Gigahertz quantized charge pumping. Nature Physics, 2007, 3, 343-347.	16.7	363
9	Magnetic Depopulation of 1D Subbands in a Narrow 2D Electron Gas in a GaAs:AlGaAs Heterojunction. Physical Review Letters, 1986, 57, 1769-1772.	7.8	342
10	All-electric all-semiconductor spin field-effect transistors. Nature Nanotechnology, 2015, 10, 35-39.	31.5	289
11	Using terahertz pulse spectroscopy to study the crystalline structure of a drug: A case study of the polymorphs of ranitidine hydrochloride. Journal of Pharmaceutical Sciences, 2003, 92, 831-838.	3.3	285
12	Terahertz pulsed imaging of skin cancer in the time and frequency domain. Journal of Biological Physics, 2003, 29, 257-259.	1.5	274
13	High-frequency single-electron transport in a quasi-one-dimensional GaAs channel induced by surface acoustic waves. Journal of Physics Condensed Matter, 1996, 8, L531-L539.	1.8	256
14	Metal-Insulator Transition at $B=0$ in a Dilute Two Dimensional GaAs-AlGaAs Hole Gas. Physical Review Letters, 1998, 80, 1292-1295.	7.8	233
15	Interaction effects in a one-dimensional constriction. Physical Review B, 1998, 58, 4846-4852.	3.2	221
16	Single-electron transport in a one-dimensional channel by high-frequency surface acoustic waves. Physical Review B, 1997, 56, 15180-15184.	3.2	219
17	Simulation of terahertz pulse propagation in biological systems. Applied Physics Letters, 2004, 84, 2190-2192.	3.3	176
18	Evolution of half plateaus as a function of electric field in a ballistic quasi-one-dimensional constriction. Physical Review B, 1991, 44, 13549-13555.	3.2	170

#	ARTICLE	IF	CITATIONS
19	Spin-triplet negatively charged excitons in GaAs quantum wells. Physical Review B, 1995, 52, 7841-7844.	3.2	163
20	Addition of the one-dimensional quantised ballistic resistance. Journal of Physics C: Solid State Physics, 1988, 21, L887-L891.	1.5	158
21	Analysis of sustained-release tablet film coats using terahertz pulsed imaging. Journal of Controlled Release, 2007, 119, 253-261.	9.9	145
22	Quantum Conductance in Silicon Oxide Resistive Memory Devices. Scientific Reports, 2013, 3, 2708.	3.3	144
23	Detection of single photons using a field-effect transistor gated by a layer of quantum dots. Applied Physics Letters, 2000, 76, 3673-3675.	3.3	142
24	Drug hydrate systems and dehydration processes studied by terahertz pulsed spectroscopy. International Journal of Pharmaceutics, 2007, 334, 78-84.	5.2	134
25	The observation of interaction and localisation effects in a two-dimensional electron gas at low temperatures. Journal of Physics C: Solid State Physics, 1980, 13, L985-L993.	1.5	133
26	Four-terminal magnetoresistance of a two-dimensional electron-gas constriction in the ballistic regime. Physical Review B, 1988, 37, 8534-8536.	3.2	130
27	Magneto-optical spectroscopy of positively charged excitons in GaAs quantum wells. Physical Review B, 1995, 52, R5523-R5526.	3.2	124
28	Clock-Controlled Emission of Single-Electron Wave Packets in a Solid-State Circuit. Physical Review Letters, 2013, 111, 216807.	7.8	112
29	Quenching of excitonic optical transitions by excess electrons in GaAs quantum wells. Physical Review B, 1995, 51, 18049-18052.	3.2	110
30	Elimination of scattering effects in spectral measurement of granulated materials using terahertz pulsed spectroscopy. Applied Physics Letters, 2008, 92, .	3.3	105
31	Anomalous Coulomb Drag in Electron-Hole Bilayers. Physical Review Letters, 2008, 101, 246801.	7.8	104
32	The transition from one- to zero-dimensional ballistic transport. Journal of Physics C: Solid State Physics, 1988, 21, L893-L898.	1.5	102
33	Vanishing hall voltage in a quasi-one-dimensional GaAs \AA Al \AA Ga \AA heterojunction. Physical Review B, 1988, 38, 8518-8521.	3.2	101
34	Spin properties of low-density one-dimensional wires. Physical Review B, 2000, 61, R13365-R13368.	3.2	99
35	Enhanced coherent terahertz emission from indium arsenide in the presence of a magnetic field. Applied Physics Letters, 2000, 76, 2038-2040.	3.3	98
36	Thermoelectric signature of the excitation spectrum of a quantum dot. Physical Review B, 1997, 55, R10197-R10200.	3.2	97

#	ARTICLE	IF	CITATIONS
37	Electrostatically defined heterojunction rings and the Aharonov-Bohm effect. Applied Physics Letters, 1989, 54, 21-23.	3.3	96
38	Crosslinked PMMA as a high-resolution negative resist for electron beam lithography and applications for physics of low-dimensional structures. Semiconductor Science and Technology, 1996, 11, 1235-1238.	2.0	96
39	Weak Localization, Hole-Hole Interactions, and the "Metal-Insulator Transition in Two Dimensions. Physical Review Letters, 2000, 84, 2489-2492.	7.8	96
40	Continuous-wave terahertz system with a 60 dB dynamic range. Applied Physics Letters, 2005, 86, 204104.	3.3	96
41	Correlation Effects on the Coupled Plasmon Modes of a Double Quantum Well. Physical Review Letters, 1997, 78, 2204-2207.	7.8	92
42	Observation of Charge Transport by Negatively Charged Excitons. Science, 2001, 294, 837-839.	12.6	88
43	Magnetotransport in a nonplanar two-dimensional electron gas. Physical Review B, 1995, 52, R8629-R8632.	3.2	86
44	Single-electron acoustic charge transport by two counterpropagating surface acoustic wave beams. Physical Review B, 1999, 60, 4850-4855.	3.2	86
45	Two-dimensional hopping conductivity in $\text{Al}_x\text{Ga}_{1-x}\text{As}$ heterostructure. Physical Review B, 1999, 59, 4580-4583.	3.2	86
46	Hole-Hole Interaction Effect in the Conductance of the Two-Dimensional Hole Gas in the Ballistic Regime. Physical Review Letters, 2002, 89, 076406.	7.8	86
47	Conductance Quantization at a Half-Integer Plateau in a Symmetric GaAs Quantum Wire. Science, 2006, 312, 1359-1362.	12.6	85
48	Zeeman Splitting in Ballistic Hole Quantum Wires. Physical Review Letters, 2006, 97, 026403.	7.8	85
49	Logarithmic corrections to two-dimensional transport in silicon inversion layers. Journal of Physics C: Solid State Physics, 1981, 14, 5737-5762.	1.5	82
50	Magnetic delocalisation of a two-dimensional electron gas and the quantum law of electron-electron scattering. Journal of Physics C: Solid State Physics, 1981, 14, L395-L402.	1.5	82
51	Thermometer for the 2D Electron Gas using 1D Thermopower. Physical Review Letters, 1998, 81, 3491-3494.	7.8	81
52	High-frequency acousto-electric single-photon source. Physical Review A, 2000, 62, .	2.5	81
53	Empirical relation between gate voltage and electrostatic potential in the one-dimensional electron gas of a split-gate device. Physical Review B, 1989, 39, 6283-6286.	3.2	77
54	Negative magnetoresistance in the variable-range-hopping regime in n-type GaAs. Physical Review B, 1989, 39, 8059-8061.	3.2	77

#	ARTICLE	IF	CITATIONS
55	Ballistic transport in one-dimensional constrictions formed in deep two-dimensional electron gases. Applied Physics Letters, 1995, 67, 109-111.	3.3	77
56	Tunneling between two-dimensional electron gases in a strong magnetic field. Physical Review B, 1994, 50, 15465-15468.	3.2	75
57	Fano Factor Reduction on the 0.7 Conductance Structure of a Ballistic One-Dimensional Wire. Physical Review Letters, 2004, 93, 116602.	7.8	75
58	Interaction Effects at Crossings of Spin-Polarized One-Dimensional Subbands. Physical Review Letters, 2003, 91, 136404.	7.8	73
59	Controlled wave-function mixing in strongly coupled one-dimensional wires. Physical Review B, 1999, 59, 12252-12255.	3.2	72
60	Incipient Formation of an Electron Lattice in a Weakly Confined Quantum Wire. Physical Review Letters, 2009, 102, 056804.	7.8	71
61	Variable-range hopping in a silicon inversion layer. Physics Letters, Section A: General, Atomic and Solid State Physics, 1974, 47, 71-72.	2.1	70
62	Non-linear conductance of a saddle-point constriction. Journal of Physics Condensed Matter, 1992, 4, 1323-1333.	1.8	70
63	Magnetic-field-induced insulator-quantum Hall-insulator transition in a disordered two-dimensional electron gas. Journal of Physics Condensed Matter, 1994, 6, 4763-4770.	1.8	70
64	Spin-dependent recombination in irradiated Si/SiO ₂ device structures. Applied Physics Letters, 1988, 52, 1161-1163.	3.3	69
65	Spin splitting of one-dimensional subbands in high quality quantum wires at zero magnetic field. Physical Review B, 2000, 62, 15842-15850.	3.2	68
66	The Aharonov-Bohm effect in electrostatically defined heterojunction rings. Journal of Physics C: Solid State Physics, 1988, 21, L325-L331.	1.5	67
67	Single-electron tunneling and Coulomb charging effects in asymmetric double-barrier resonant-tunneling diodes. Physical Review B, 1992, 45, 14407-14410.	3.2	67
68	Screening of the surface-acoustic-wave potential by a metal gate and the quantization of the acoustoelectric current in a narrow channel. Physical Review B, 1998, 58, 10589-10596.	3.2	67
69	Observation of Coulomb blockade oscillations in the thermopower of a quantum dot. Solid State Communications, 1993, 87, 1145-1149.	1.9	66
70	Single-electron acoustic charge transport on shallow-etched channels in a perpendicular magnetic field. Physical Review B, 2000, 62, 1564-1567.	3.2	66
71	Charging and double-frequency Aharonov-Bohm effects in an open system. Physical Review B, 1994, 49, 17456-17459.	3.2	65
72	Quantized acoustoelectric current transport through a static quantum dot using a surface acoustic wave. Physical Review B, 2003, 68, .	3.2	65

#	ARTICLE	IF	CITATIONS
73	Terahertz pulsed imaging as an analytical tool for sustained-release tablet film coating. <i>European Journal of Pharmaceutics and Biopharmaceutics</i> , 2009, 71, 117-123.	4.3	64
74	Time-of-Flight Measurements of Single-Electron Wave Packets in Quantum Hall Edge States. <i>Physical Review Letters</i> , 2016, 116, 126803.	7.8	64
75	One-dimensional quantised ballistic resistors in parallel configuration. <i>Journal of Physics Condensed Matter</i> , 1989, 1, 6763-6770.	1.8	63
76	On the acoustoelectric current in a one-dimensional channel. <i>Journal of Physics Condensed Matter</i> , 1996, 8, L337-L343.	1.8	63
77	Resistance resonance induced by electron-hole hybridization in a strongly coupled InAs/GaSb/AlSb heterostructure. <i>Physical Review B</i> , 1998, 57, 11915-11918.	3.2	62
78	Optically induced bistability in the mobility of a two-dimensional electron gas coupled to a layer of quantum dots. <i>Applied Physics Letters</i> , 1999, 74, 735-737.	3.3	62
79	Noise and reproducible structure in a GaAs/Al _x Ga _{1-x} As one-dimensional channel. <i>Physical Review B</i> , 1991, 44, 1938-1941.	3.2	61
80	Reentrant Insulator-Metal-Insulator Transition at $B=0$ in a Two-Dimensional Hole Gas. <i>Physical Review Letters</i> , 1999, 82, 1542-1545.	7.8	60
81	Transport in a superlattice of 1D ballistic channels. <i>Journal of Physics Condensed Matter</i> , 1990, 2, 3405-3414.	1.8	59
82	Ballistic transport in one dimension: additional quantisation produced by an electric field. <i>Journal of Physics Condensed Matter</i> , 1990, 2, 7247-7254.	1.8	59
83	Influence of excess electrons and magnetic fields on Mott-Wannier excitons in GaAs quantum wells. <i>Advances in Physics</i> , 1995, 44, 47-72.	14.4	59
84	Coherent Time Evolution of a Single-Electron Wave Function. <i>Physical Review Letters</i> , 2009, 102, 156801.	7.8	59
85	Properties of a ballistic quasi-one-dimensional constriction in a parallel high magnetic field. <i>Physical Review B</i> , 1991, 44, 10973-10975.	3.2	58
86	Spectroscopy of a two-dimensional electron gas in the quantum-Hall-effect regime by use of low-frequency edge magnetoplasmons. <i>Physical Review B</i> , 1992, 46, 12427-12432.	3.2	58
87	Photoluminescence due to positively charged excitons in undoped GaAs/Al _x Ga _{1-x} As quantum wells. <i>Physical Review B</i> , 1996, 53, 13002-13010.	3.2	57
88	Coulomb interaction of two electrons in the quantum dot formed by the surface acoustic wave in a narrow channel. <i>Physical Review B</i> , 1999, 60, R13954-R13957.	3.2	57
89	Kondo Effect from a Tunable Bound State within a Quantum Wire. <i>Physical Review Letters</i> , 2008, 100, 026807.	7.8	57
90	Length Scales at the Metal-Insulator Transition in Compensated GaAs. <i>Physical Review Letters</i> , 1988, 61, 369-372.	7.8	55

#	ARTICLE	IF	CITATIONS
91	Direct experimental determination of the tunnelling time and transmission probability of electrons through a resonant tunnelling structure. <i>Journal of Physics Condensed Matter</i> , 1991, 2, 8969-8975.	1.8	55
92	Fabrication of high-quality one- and two-dimensional electron gases in undoped GaAs/AlGaAs heterostructures. <i>Applied Physics Letters</i> , 1999, 74, 2328-2330.	3.3	54
93	Direction-resolved transport and possible many-body effects in one-dimensional thermopower. <i>Physical Review B</i> , 2000, 62, R16275-R16278.	3.2	54
94	Chemical mapping using reflection terahertz pulsed imaging. <i>Semiconductor Science and Technology</i> , 2005, 20, S254-S257.	2.0	54
95	An accurate high-speed single-electron quantum dot pump. <i>New Journal of Physics</i> , 2010, 12, 073013.	2.9	54
96	Quantized charge pumping through a quantum dot by surface acoustic waves. <i>Applied Physics Letters</i> , 2004, 84, 4319-4321.	3.3	53
97	Universal conductance fluctuations and electron coherence lengths in a narrow two-dimensional electron gas. <i>Physical Review B</i> , 1987, 36, 4514-4517.	3.2	52
98	Possible Evidence of a Spontaneous Spin Polarization in Mesoscopic Two-Dimensional Electron Systems. <i>Physical Review Letters</i> , 2004, 92, 116601.	7.8	52
99	Resonant tunneling between parallel, two-dimensional electron gases: A new approach to device fabrication using in situ ion beam lithography and molecular beam epitaxy growth. <i>Applied Physics Letters</i> , 1994, 64, 1827-1829.	3.3	51
100	Wave functions and Fermi surfaces of strongly coupled two-dimensional electron gases investigated by in-plane magnetoresistance. <i>Physical Review B</i> , 1994, 50, 4889-4892.	3.2	51
101	Magnetization Instability in a Two-Dimensional System. <i>Physical Review Letters</i> , 1997, 79, 4449-4452.	7.8	51
102	Spin-dependent transport in a quasiballistic quantum wire. <i>Physical Review B</i> , 2000, 61, 9952-9955.	3.2	51
103	Resonant magneto-transport through a lateral quantum box in a semiconductor heterostructure. <i>Journal of Physics Condensed Matter</i> , 1989, 1, 6291-6298.	1.8	50
104	Experimental Evidence for Coulomb Charging Effects in an Open Quantum Dot at Zero Magnetic Field. <i>Physical Review Letters</i> , 1998, 81, 3507-3510.	7.8	50
105	Localisation in disordered two-dimensional systems and the universal dependence on diffusion length. <i>Journal of Physics C: Solid State Physics</i> , 1981, 14, L413-L419.	1.5	49
106	Effect of spatial dispersion on acoustoelectric current in a high-mobility two-dimensional electron gas. <i>Physical Review B</i> , 1995, 51, 14770-14773.	3.2	49
107	Weak localization in high-quality two-dimensional systems. <i>Physical Review B</i> , 2004, 70, .	3.2	49
108	Resonant tunneling in an $\text{Al}_x\text{Ga}_{1-x}\text{As}$ /GaAs quantum dot as a function of magnetic field. <i>Physical Review B</i> , 1992, 46, 3948-3952.	3.2	48

#	ARTICLE	IF	CITATIONS
109	Spin injection between epitaxial Co ₂ Mn _{1.6} Ga and an InGaAs quantum well. Applied Physics Letters, 2005, 86, 252106.	3.3	48
110	Enhanced g factors of a one-dimensional hole gas with quantized conductance. Physical Review B, 1997, 55, R13409-R13412.	3.2	47
111	Magneto-resistance oscillations and the transition from three-dimensional to two-dimensional conduction in a gallium arsenide field effect transistor at low temperatures. Journal of Physics C: Solid State Physics, 1982, 15, L21-L30.	1.5	46
112	The growth and physics of high mobility two-dimensional hole gases. Journal of Crystal Growth, 1991, 111, 318-322.	1.5	46
113	Charging effects and the excitation spectrum of a quantum dot formed by an impurity potential. Physical Review B, 1993, 48, 8866-8871.	3.2	46
114	Bias-controlled spin polarization in quantum wires. Applied Physics Letters, 2008, 93, .	3.3	46
115	Possible observation of an electronic phase transition in Sb doped Si. Journal of Physics C: Solid State Physics, 1984, 17, L425-L432.	1.5	45
116	Enhanced current quantization in high-frequency electron pumps in a perpendicular magnetic field. Physical Review B, 2008, 78, .	3.2	45
117	Ground State of a Two-Dimensional Coupled Electron-Hole Gas in InAs/GaSb Narrow Gap Heterostructures. Physical Review Letters, 1999, 82, 2362-2365.	7.8	44
118	Spin-Incoherent Transport in Quantum Wires. Physical Review Letters, 2008, 101, 036801.	7.8	44
119	Anderson localisation of holes in a Si inversion layer. Physics Letters, Section A: General, Atomic and Solid State Physics, 1974, 48, 113-114.	2.1	43
120	Magnetic localization in silicon inversion layers. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1978, 37, 83-95.	0.6	43
121	Time-irreversible random telegraph signal due to current along a single hopping chain. Physical Review Letters, 1992, 69, 502-505.	7.8	43
122	Realization of quantum-dot cellular automata using semiconductor quantum dots. Superlattices and Microstructures, 2003, 34, 195-203.	3.1	43
123	Energy-Dependent Tunneling from Few-Electron Dynamic Quantum Dots. Physical Review Letters, 2007, 99, 156802.	7.8	43
124	The transition from two- to one-dimensional electronic transport in narrow silicon accumulation layers. Journal of Physics C: Solid State Physics, 1982, 15, L1287-L1297.	1.5	42
125	Closely separated one-dimensional wires:. Physica B: Condensed Matter, 1998, 249-251, 157-161.	2.7	42
126	Conductance quantization and the $0.7\hbar/2e\hbar$ conductance anomaly in one-dimensional hole systems. Applied Physics Letters, 2006, 88, 012107.	3.3	42

#	ARTICLE	IF	CITATIONS
127	Zero-bias anomaly in quantum wires. Physical Review B, 2009, 79, .	3.2	42
128	Quantum magnetic confinement in a curved two-dimensional electron gas. Journal of Physics Condensed Matter, 1994, 6, L127-L134.	1.8	41
129	Electric-field-induced ionization of negatively charged excitons in quantum wells. Physical Review B, 1997, 55, R1970-R1972.	3.2	41
130	Application of terahertz pulsed imaging to analyse film coating characteristics of sustained-release coated pellets. International Journal of Pharmaceutics, 2013, 457, 521-526.	5.2	41
131	Electron-electron scattering in silicon inversion layers. Journal of Physics C: Solid State Physics, 1983, 16, L353-L360.	1.5	40
132	Critical conductivity at the magnetic-field-induced metal-insulator transition in n-GaAs and n-InSb. Journal of Physics C: Solid State Physics, 1986, 19, 3983-3990.	1.5	40
133	Electron transport in a non-uniform magnetic field. Journal of Physics Condensed Matter, 1995, 7, L307-L315.	1.8	40
134	Frictional drag between parallel two-dimensional electron gases in a perpendicular magnetic field. Journal of Physics Condensed Matter, 1996, 8, L557-L562.	1.8	40
135	Parallel quantized charge pumping. Physical Review B, 2009, 80, .	3.2	40
136	Row coupling in an interacting quasi-one-dimensional quantum wire investigated using transport measurements. Physical Review B, 2009, 80, .	3.2	40
137	Fabry-Perot interferometry with electron waves. Journal of Physics Condensed Matter, 1989, 1, 9035-9044.	1.8	39
138	Aharonovâ€“Bohm effect and oneâ€“dimensional ballistic transport through two independent parallel channels. Applied Physics Letters, 1993, 63, 3191-3193.	3.3	39
139	Rapid radiative decay of charged excitons. Physical Review B, 2000, 62, R13294-R13297.	3.2	39
140	Impact of long- and short-range disorder on the metallic behaviour of two-dimensional systems. Nature Physics, 2008, 4, 55-59.	16.7	39
141	The spatial extent of localized state wavefunctions in silicon inversion layers. Journal of Physics C: Solid State Physics, 1974, 7, L273-L277.	1.5	37
142	Magnetotunneling spectroscopy of one-dimensional wires. Physical Review B, 1997, 55, R1966-R1969.	3.2	37
143	Fabrication and transport properties of clean long one-dimensional quantum wires formed in modulation-doped GaAs/AlGaAs heterostructures. Applied Physics Letters, 1999, 75, 2975-2977.	3.3	37
144	Logarithmic and power law corrections in two-dimensional electronic transport. Journal of Physics C: Solid State Physics, 1982, 15, L371-L376.	1.5	36

#	ARTICLE	IF	CITATIONS
145	Electron-electron scattering in narrow Si accumulation layers. Journal of Physics Condensed Matter, 1989, 1, 3289-3293.	1.8	36
146	Study of the carrier density dependence of the frictional drag between closely spaced two-dimensional electron gases. Semiconductor Science and Technology, 1995, 10, 1229-1232.	2.0	36
147	Negatively charged excitons in coupled double quantum wells. Physical Review B, 1997, 55, 1318-1321.	3.2	36
148	Quantum magnetic confinement and transport in spherical two-dimensional electron gases. Physical Review B, 1995, 52, R8646-R8649.	3.2	35
149	Transport properties of two-dimensional electron gases containing InAs self-assembled dots. Applied Physics Letters, 1998, 73, 2468-2470.	3.3	35
150	Fermi-Liquid Behavior of the Low-Density 2D Hole Gas in aGaAs/AlGaAsHeterostructure at Large Values of μ . Physical Review Letters, 2001, 86, 4895-4898.	7.8	35
151	Dephasing in an isolated double-quantum-dot system deduced from single-electron polarization measurements. Physical Review B, 2003, 67, .	3.2	35
152	Single-Electron Population and Depopulation of an Isolated Quantum Dot Using a Surface-Acoustic-Wave Pulse. Physical Review Letters, 2007, 98, 046801.	7.8	35
153	The Anderson transition in silicon inversion layers. Surface Science, 1976, 58, 79-88.	1.9	34
154	Metal-insulator transitions induced by a magnetic field. Journal of Non-Crystalline Solids, 1979, 32, 161-185.	3.1	34
155	Observation of Aharonov-Bohm oscillations in a narrow two-dimensional electron gas. Journal of Physics Condensed Matter, 1989, 1, 3369-3373.	1.8	34
156	Quantized current in one-dimensional channel induced by surface acoustic waves. Physica B: Condensed Matter, 1998, 249-251, 140-146.	2.7	34
157	A metal-insulator transition in the impurity band of n-type GaAs induced by loss of dimension. Journal of Physics C: Solid State Physics, 1977, 10, L173-L177.	1.5	33
158	Experimental investigation of the surface acoustic wave electron capture mechanism. Physical Review B, 2006, 74, .	3.2	33
159	Electrons in one dimension. Philosophical Transactions Series A, Mathematical, Physical, and Engineering Sciences, 2010, 368, 1141-1162.	3.4	33
160	Spin-orbit coupling and weak localisation in the 2D inversion layer of indium phosphide. Journal of Physics C: Solid State Physics, 1982, 15, L1137-L1145.	1.5	32
161	An experimental test of the scaling theory of conduction in two dimensions. Journal of Physics C: Solid State Physics, 1983, 16, L285-L289.	1.5	32
162	Back-gated split-gate transistor: A one-dimensional ballistic channel with variable Fermi energy. Applied Physics Letters, 1992, 60, 2782-2784.	3.3	32

#	ARTICLE	IF	CITATIONS
163	A new mechanism for high-frequency rectification in a ballistic quantum point contact. Journal of Physics Condensed Matter, 1994, 6, L163-L168.	1.8	32
164	Energy-level pinning and the 0.7 spin state in one dimension: GaAs quantum wires studied using finite-bias spectroscopy. Physical Review B, 2007, 75, .	3.2	32
165	The observation of localisation and interaction effects in the two-dimensional electron gas of a GaAs-GaAlAs heterojunction at low temperatures. Journal of Physics C: Solid State Physics, 1981, 14, L995-L1005.	1.5	31
166	Electronic instabilities in the hot-electron regime of the one-dimensional ballistic resistor. Journal of Physics Condensed Matter, 1989, 1, 6285-6290.	1.8	31
167	Experimental study of the acoustoelectric effects in GaAs-AlGaAs heterostructures. Journal of Physics Condensed Matter, 1995, 7, 7675-7685.	1.8	31
168	Magnetic separation of localisation and interaction effects in a two-dimensional electron gas at low temperatures. Journal of Physics C: Solid State Physics, 1981, 14, L531-L537.	1.5	30
169	The frequency effect and the quantised Hall resistance. Journal of Physics C: Solid State Physics, 1983, 16, L113-L117.	1.5	30
170	The Aharonov-Bohm effect in the fractional quantum Hall regime. Surface Science, 1996, 361-362, 17-21.	1.9	30
171	Fractional quantum Hall effect in bilayer two-dimensional hole-gas systems. Physical Review B, 1996, 54, R5259-R5262.	3.2	30
172	Metallic Behavior in Dilute Two-Dimensional Hole Systems. Physical Review Letters, 2001, 87, 126802.	7.8	30
173	Conductance oscillations in a two-dimensional impurity band. Journal of Physics C: Solid State Physics, 1979, 12, L617-L625.	1.5	29
174	The magnetic field induced metal-insulator transition in n-type InP. Journal of Physics C: Solid State Physics, 1984, 17, 3391-3400.	1.5	29
175	Distribution-function analysis of mesoscopic hopping conductance fluctuations. Physical Review B, 1996, 54, 2091-2100.	3.2	29
176	Ultrafast voltage sampling using single-electron wavepackets. Applied Physics Letters, 2017, 110, .	3.3	29
177	Spin-dependent and localisation effects at Si/SiO ₂ device interfaces. Semiconductor Science and Technology, 1989, 4, 1045-1060.	2.0	28
178	Resonant transmission through an open quantum dot. Physical Review B, 1997, 55, 6723-6726.	3.2	28
179	All-Electrical Injection and Detection of a Spin-Polarized Current Using 1D Conductors. Physical Review Letters, 2012, 109, 177202.	7.8	28
180	One-dimensional ballistic resistor in hot-electron regime: nonlinear and negative differential resistance to 10 THz. Electronics Letters, 1989, 25, 992.	1.0	27

#	ARTICLE	IF	CITATIONS
181	Electron-density-dependent optical spectra of a remotely-doped GaAs/Al _{0.33} Ga _{0.67} As single quantum well. Superlattices and Microstructures, 1994, 15, 355.	3.1	27
182	Fabrication of high mobility in situ back-gated (311)A hole gas heterojunctions. Applied Physics Letters, 1997, 70, 2750-2752.	3.3	27
183	Excitonic recombination processes in spin-polarized two-dimensional electron gases. Physical Review B, 1998, 58, R4227-R4230.	3.2	27
184	Influence of parallel magnetic fields on a single-layer two-dimensional electron system with a hopping mechanism of conductivity. Physical Review B, 2000, 61, 7253-7256.	3.2	27
185	0.7 Structure and Zero Bias Anomaly in Ballistic Hole Quantum Wires. Physical Review Letters, 2008, 100, 016403.	7.8	27
186	LO-Phonon Emission Rate of Hot Electrons from an On-Demand Single-Electron Source in a GaAs/AlGaAs Heterostructure. Physical Review Letters, 2018, 121, 137703.	7.8	27
187	Activationless hopping of correlated electrons in n-type GaAs. Physical Review B, 1989, 40, 3387-3389.	3.2	26
188	Terahertz pulse imaging of in-vitro basal cell carcinoma samples. , 2001, , .		26
189	Measurements of noise caused by switching of impurity states and of suppression of shot noise in surface-acoustic-wave-based single-electron pumps. Physical Review B, 2002, 65, .	3.2	26
190	Quantum-dot thermometry of electron heating by surface acoustic waves. Applied Physics Letters, 2006, 89, 122104.	3.3	26
191	The effect of pulse-modulated surface acoustic waves on acoustoelectric current quantization. Journal of Applied Physics, 2006, 100, 063710.	2.5	26
192	Phase coherence, interference, and conductance quantization in a confined two-dimensional hole gas. Physical Review B, 1994, 49, 5101-5104.	3.2	25
193	General picture of quantum Hall transitions in quantum antidots. Physical Review B, 1995, 52, R8672-R8675.	3.2	25
194	Coulomb Blockade as a Noninvasive Probe of Local Density of States. Physical Review Letters, 1996, 77, 350-353.	7.8	25
195	Electrical properties of two-dimensional electron gases grown on cleaned SiGe virtual substrates. Thin Solid Films, 1998, 321, 181-185.	1.8	25
196	Origin of the Oscillator Strength of the Triplet State of a Trion in a Magnetic Field. Physical Review Letters, 2002, 89, 246805.	7.8	25
197	Crossover phenomenon for two-dimensional hopping conductivity and density-of-states near the Fermi level. Solid State Communications, 1999, 109, 751-756.	1.9	24
198	Non-Kondo zero-bias anomaly in quantum wires. Physical Review B, 2009, 79, .	3.2	24

#	ARTICLE	IF	CITATIONS
199	The magnetic field induced metal-insulator transition in indium phosphide and silicon. Solid-State Electronics, 1985, 28, 61-72.	1.4	23
200	Fractional quantum Hall effect in high-mobility two-dimensional hole gases in tilted magnetic fields. Physical Review B, 1991, 44, 13128-13131.	3.2	23
201	Effect of terahertz irradiation on ballistic transport through one-dimensional quantum point contacts. Applied Physics Letters, 1995, 66, 3149-3151.	3.3	23
202	Comparison of optical and transport measurements of electron densities in quantum wells. Semiconductor Science and Technology, 1996, 11, 890-896.	2.0	23
203	Quantum transport in In _{0.75} Ga _{0.25} As quantum wires. Applied Physics Letters, 2008, 92, 152108.	3.3	23
204	Evidence of a magnetic-field-induced insulator-metal-insulator transition. Physical Review B, 1989, 39, 1430-1433.	3.2	22
205	Thermopower of a one-dimensional ballistic constriction in the non-linear regime. Journal of Physics Condensed Matter, 1993, 5, 8055-8064.	1.8	22
206	The metal-insulator transition in the impurity band of n-type GaAs induced by a magnetic field and loss of dimension. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1978, 37, 187-198.	0.6	21
207	Spin dependent surface recombination in silicon p-n junctions: The effect of irradiation. Solid State Communications, 1980, 34, 803-805.	1.9	21
208	One-dimensional electron localisation and conduction of electron-electron scattering in narrow silicon MOSFETS. Journal of Physics C: Solid State Physics, 1984, 17, 5663-5676.	1.5	21
209	Quantum corrections and the metal-insulator transition as a function of dimensionality in the GaAs impurity band. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1985, 52, 437-458.	0.6	21
210	Electron state lifetimes in submicron diameter resonant tunneling diodes. Applied Physics Letters, 1991, 59, 1966-1968.	3.3	21
211	Vertical tunneling between two quantum dots in a transverse magnetic field. Physical Review B, 1994, 49, 8071-8075.	3.2	21
212	Charge oscillations in edge states and double-frequency Aharonov-Bohm effects around a tunable obstacle. Surface Science, 1994, 305, 453-459.	1.9	21
213	Low temperature characterization of modulation doped SiGe grown on bonded silicon-insulator. Applied Physics Letters, 1996, 69, 2704-2706.	3.3	21
214	Cyclotron-resonance studies of strongly coupled double quantum wells in tilted magnetic fields near the quantum and semiclassical limits. Physical Review B, 1997, 56, R4340-R4343.	3.2	21
215	Spin-dependent transport in a clean one-dimensional channel. Physical Review B, 1999, 60, 10687-10690.	3.2	21
216	The two-dimensional lateral injection in-plane laser. IEEE Journal of Quantum Electronics, 1999, 35, 352-357.	1.9	21

#	ARTICLE	IF	CITATIONS
217	Universality at a quantum Hall–Hall insulator transition in a Si/Si _{0.87} Ge _{0.13} 2D hole system. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2000, 6, 297-300.	2.7	21
218	Ballistic transport in a GaAs/Al _x Ga _{1-x} As one-dimensional channel fabricated using an atomic force microscope. <i>Applied Physics Letters</i> , 2001, 78, 3466-3468.	3.3	21
219	Relative importance of the electron interaction strength and disorder in the two-dimensional metallic state. <i>Physical Review B</i> , 2002, 66, .	3.2	21
220	Controlled spatial separation of spins and coherent dynamics in spin-orbit-coupled nanostructures. <i>Nature Communications</i> , 2017, 8, 15997.	12.8	21
221	The Wigner glass and conductance oscillations in silicon inversion layers. <i>Journal of Physics C: Solid State Physics</i> , 1982, 15, L617-L625.	1.5	20
222	Direct measurement of the thermal conductivity of a two-dimensional electron gas. <i>Journal of Physics Condensed Matter</i> , 1989, 1, 3375-3380.	1.8	20
223	The one dimensional quantised ballistic resistance in GaAs/AlGaAs heterojunctions with varying experimental conditions. <i>Solid-State Electronics</i> , 1989, 32, 1179-1183.	1.4	20
224	Two-dimensional electron-gas heating and phonon emission by hot ballistic electrons. <i>Physical Review B</i> , 1992, 45, 6309-6312.	3.2	20
225	Compressibility studies of double electron and double hole gas systems. <i>Applied Physics Letters</i> , 1996, 68, 3323-3325.	3.3	20
226	Nonlinear transport in a single-mode one-dimensional electron gas. <i>The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties</i> , 1998, 77, 1213-1218.	0.6	20
227	Fabrication of closely spaced, independently contacted electron-hole bilayers in GaAs-AlGaAs heterostructures. <i>Applied Physics Letters</i> , 2005, 87, 202104.	3.3	20
228	Spin injection from Co ₂ MnGa into an InGaAs quantum well. <i>Applied Physics Letters</i> , 2008, 92, 232101.	3.3	20
229	Field-induced modulation of the conductance, thermoelectric power, and magnetization in ballistic coupled double quantum wires under a tilted magnetic field. <i>Physical Review B</i> , 2008, 77, .	3.2	20
230	Zero-Magnetic Field Fractional Quantum States. <i>Physical Review Letters</i> , 2019, 122, 086803.	7.8	20
231	One dimensional electron tunneling and related phenomena. <i>Surface Science</i> , 1990, 228, 387-392.	1.9	19
232	Metal–insulator transition at B=0 in an ultra-low density two-dimensional hole gas. <i>Physica B: Condensed Matter</i> , 1998, 249-251, 705-709.	2.7	19
233	Effects of magnetic field and optical fluence on terahertz emission in gallium arsenide. <i>Physical Review B</i> , 2001, 64, .	3.2	19
234	Experimental Progress towards Probing the Ground State of an Electron-Hole Bilayer by Low-Temperature Transport. <i>Advances in Condensed Matter Physics</i> , 2011, 2011, 1-22.	1.1	19

#	ARTICLE	IF	CITATIONS
235	V. The Hall effect in impurity bands and inversion layers. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1978, 38, 515-526.	0.6	18
236	Localization and quantization in silicon inversion layers. Contemporary Physics, 1985, 26, 257-293.	1.8	18
237	Large transconductances observed in an independently contacted coupled double quantum well. Applied Physics Letters, 1994, 64, 3018-3020.	3.3	18
238	Hydrogen radical surface cleaning of GaAs for MBE regrowth. Journal of Crystal Growth, 1997, 175-176, 416-421.	1.5	18
239	Local transport in a disorder-stabilized correlated insulating phase. Physical Review B, 2005, 72, .	3.2	18
240	Energy loss rate in silicon inversion layers. Journal of Physics C: Solid State Physics, 1983, 16, L291-L299.	1.5	17
241	Frequency-enhanced fractional quantisation in GaAs-GaAlAs heterojunctions. Journal of Physics C: Solid State Physics, 1984, 17, L439-L444.	1.5	17
242	Two-terminal conductance of the quantised Hall resistor. Journal of Physics C: Solid State Physics, 1984, 17, L359-L364.	1.5	17
243	Magnetic depopulation of sub-bands in In _{0.53} Ga _{0.47} As/In _{0.52} Al _{0.48} As heterojunctions. Journal of Physics C: Solid State Physics, 1986, 19, L403-L410.	1.5	17
244	Molecular beam epitaxial growth and magneto-transport studies of the InSb/CdTe material systems. Semiconductor Science and Technology, 1990, 5, S311-S314.	2.0	17
245	The Aharonov-Bohm effect in the fractional quantum Hall regime. Journal of Physics Condensed Matter, 1994, 6, L725-L730.	1.8	17
246	Experimental investigation of the damping of low-frequency edge magnetoplasmons in GaAs-AlxGa _{1-x} As heterostructures. Physical Review B, 1994, 50, 1582-1587.	3.2	17
247	Direct Measurement of the Band Structure of a One-Dimensional Surface Superlattice. Physical Review Letters, 1996, 76, 3802-3805.	7.8	17
248	Enhanced coherent terahertz emission from indium arsenide. Journal of Modern Optics, 2000, 47, 1847-1856.	1.3	17
249	High-sensitivity colorimetric detection of DNA hybridization on a gold surface with high spatial resolution. Nanotechnology, 2003, 14, 7-10.	2.6	17
250	Influence of the Thiol Position on the Attachment and Subsequent Hybridization of Thiolated DNA on Gold Surfaces. Langmuir, 2004, 20, 1527-1530.	3.5	17
251	Low temperature transport in undoped mesoscopic structures. Applied Physics Letters, 2009, 94, 172105.	3.3	17
252	Self-organised fractional quantisation in a hole quantum wire. Journal of Physics Condensed Matter, 2018, 30, 09LT01.	1.8	17

#	ARTICLE	IF	CITATIONS
253	Cation transport in SiO ₂ . Physica Status Solidi A, 1972, 12, 199-207.	1.7	16
254	An introduction to silicon inversion layers. Contemporary Physics, 1977, 18, 423-454.	1.8	16
255	Ballistic injection of electrons in metal-semiconductor junctions. I. Phonon spectroscopy and impurity-enhanced inelastic scattering in n+silicon. Journal of Physics C: Solid State Physics, 1980, 13, L709-L716.	1.5	16
256	The smallest length scale near the metal-insulator transition. Journal of Physics C: Solid State Physics, 1987, 20, L19-L24.	1.5	16
257	Quantum interference in variable range hopping under directional constraints. Physical Review B, 1989, 40, 10052-10055.	3.2	16
258	Electron Density Dependence of the Excitonic Absorption Thresholds of GaAs Quantum Wells. Physica Status Solidi A, 2000, 178, 465-470.	1.7	16
259	Coulomb charging effects in an open quantum dot device. Journal of Physics Condensed Matter, 2001, 13, 9515-9534.	1.8	16
260	Inversion Layer Transport and the Radiation Hardness of the Si-SiO ₂ Interface. IEEE Transactions on Nuclear Science, 1978, 25, 1283-1287.	2.0	15
261	Loss of dimensionality, localisation and conductance oscillations in N-type GaAs FET's. Physica B: Physics of Condensed Matter & C: Atomic, Molecular and Plasma Physics, Optics, 1983, 117-118, 697-699.	0.9	15
262	Low-frequency edge excitations in an electrostatically confined GaAs-AlGaAs two-dimensional electron gas. Journal of Physics Condensed Matter, 1993, 5, 7643-7648.	1.8	15
263	Electronic properties of a one-dimensional channel field effect transistor formed by molecular beam epitaxial regrowth on patterned GaAs. Applied Physics Letters, 1993, 63, 2219-2221.	3.3	15
264	Single-electron tunneling and Coulomb charging effects in ultras-small double-barrier heterostructures. Solid-State Electronics, 1994, 37, 793-799.	1.4	15
265	Noninvasive detection of the evolution of the charge states of a double dot system. Physical Review B, 2004, 69, .	3.2	15
266	Evolution of the bilayer $\nu=1$ quantum Hall state under charge imbalance. Physical Review B, 2005, 71, .	3.2	15
267	Anomalous spin-dependent behavior of one-dimensional subbands. Physical Review B, 2005, 72, .	3.2	15
268	Possible effect of collective modes in zero magnetic field transport in an electron-hole bilayer. Physical Review B, 2009, 80, .	3.2	15
269	Frequency-induced electron delocalisation and fractional quantisation in silicon inversion layers. Journal of Physics C: Solid State Physics, 1984, 17, L433-L438.	1.5	14
270	Conductance fluctuations from the local alteration of a hopping path. Journal of Physics Condensed Matter, 1989, 1, 8481-8489.	1.8	14

#	ARTICLE	IF	CITATIONS
271	The thermoelectric effect in silicon on sapphire inversion layers. Superlattices and Microstructures, 1989, 5, 103-107.	3.1	14
272	Quantum ballistic transport through a zero-dimensional structure. Superlattices and Microstructures, 1989, 5, 599-602.	3.1	14
273	Electron interactions in the two-dimensional electron-gas base of a vertical hot-electron transistor. Physical Review B, 1990, 42, 11415-11418.	3.2	14
274	Multilayered gated lateral quantum dot devices. Applied Physics Letters, 2000, 76, 1134-1136.	3.3	14
275	Effect of screening long-range Coulomb interactions on the metallic behavior in two-dimensional hole systems. Physical Review B, 2008, 77, .	3.2	14
276	Nuclear spin coherence in a quantum wire. Physical Review B, 2009, 80, .	3.2	14
277	Odd-even spin effects and variation of $\langle \sigma \rangle$ factor in a quasi-one-dimensional subband. Physical Review B, 2009, 79, .	3.2	14
278	Compressibility Measurements of Quasi-One-Dimensional Quantum Wires. Physical Review Letters, 2011, 107, 126801.	7.8	14
279	Electron transport in silicon inversion layers at high magnetic fields and the influence of substrate bias. Surface Science, 1980, 98, 283-298.	1.9	13
280	Tunneling between totally quantized levels in GaAs/AlGaAs asymmetric triple-barrier heterostructures in high magnetic fields. Applied Physics Letters, 1991, 59, 803-805.	3.3	13
281	Observation of quantum interference in thermoelectric transport. Physical Review Letters, 1991, 66, 1622-1625.	7.8	13
282	The fractional quantum Hall effect in high mobility two-dimensional hole gases. Surface Science, 1992, 263, 81-86.	1.9	13
283	Resonant resistance enhancement in double-quantum-well GaAs-AlxGa $_{1-x}$ As heterostructures. Physical Review B, 1994, 50, 8024-8027.	3.2	13
284	Analytical model of a one-dimensional constriction with many occupied subbands: Calculation and experiment. Physical Review B, 1994, 49, 11500-11503.	3.2	13
285	Resistance fluctuations in diffusive transport at high magnetic fields in narrow Si transistors. Physical Review B, 1994, 50, 12187-12190.	3.2	13
286	Surface decontamination of patterned GaAs substrates for molecular beam epitaxy regrowth using a hydrogen radical source. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1997, 15, 325.	1.6	13
287	Magnetoplasmons in a Tunable Periodically Modulated Magnetic Field. Physical Review Letters, 1999, 83, 4425-4428.	7.8	13
288	Localisation and the metal-insulator transition in two dimensions. Physica B: Condensed Matter, 2001, 296, 21-31.	2.7	13

#	ARTICLE	IF	CITATIONS
289	Tuning the electron transport properties of a one-dimensional constriction using hydrostatic pressure. <i>Physical Review B</i> , 2002, 65, .	3.2	13
290	Electron Assisted Variable Range Hopping in Strongly Correlated 2D Electron Systems. <i>Physica Status Solidi (B): Basic Research</i> , 2002, 230, 211-216.	1.5	13
291	Magnetic-field-induced enhancement of terahertz emission from III-V semiconductor surfaces. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2002, 13, 896-899.	2.7	13
292	Optical imaging of trion diffusion and drift in GaAs quantum wells. <i>Physical Review B</i> , 2003, 68, .	3.2	13
293	Acoustoelectric current transport through a double quantum dot. <i>Physical Review B</i> , 2005, 72, .	3.2	13
294	Acoustoelectric current in submicron-separated quantum wires. <i>Applied Physics Letters</i> , 2005, 86, 152105.	3.3	13
295	Examination of surface acoustic wave reflections by observing acoustoelectric current generation under pulse modulation. <i>Applied Physics Letters</i> , 2006, 89, 132102.	3.3	13
296	Fano effect and Kondo effect in quantum dots formed in strongly coupled quantum wells. <i>Physical Review B</i> , 2006, 73, .	3.2	13
297	Observation of localisation and interaction corrections to the conductivity and thermopower of a two-dimensional electron gas. <i>Journal of Physics Condensed Matter</i> , 1989, 1, 2747-2753.	1.8	12
298	Two-dimensional electron gas base hot electron transistor. <i>Electronics Letters</i> , 1990, 26, 862.	1.0	12
299	Hopping in a low-mobility GaAs-AlGaAs heterojunction in the limit of low electronic concentrations. <i>Journal of Physics Condensed Matter</i> , 1990, 2, 7367-7371.	1.8	12
300	Dissipative tunneling in two-state systems at the Si/SiO ₂ interface. <i>Physical Review Letters</i> , 1993, 71, 4230-4233.	7.8	12
301	Transition from one- to two-subband occupancy in the 2DEG of back-gated modulation-doped GaAs-Al _x Ga _{1-x} As heterostructures. <i>Physical Review B</i> , 1995, 51, 17600-17604.	3.2	12
302	Measurements of a composite fermion split-gate device. <i>Physical Review B</i> , 1996, 53, R7596-R7598.	3.2	12
303	Electron reflection and interference in the GaAs/AlAs-Al Schottky collector resonant-tunneling diode. <i>Physical Review B</i> , 1998, 57, 1847-1854.	3.2	12
304	Dynamic localization of two-dimensional electrons at mesoscopic length scales. <i>Physical Review B</i> , 2004, 70, .	3.2	12
305	Noninvasive lateral detection of Coulomb blockade in a quantum dot fabricated using atomic force microscopy. <i>Journal of Applied Physics</i> , 2004, 95, 2557-2559.	2.5	12
306	Zero-Bias Anomaly and Kondo-Assisted Quasiballistic 2D Transport. <i>Physical Review Letters</i> , 2005, 95, 066603.	7.8	12

#	ARTICLE	IF	CITATIONS
307	Bychkovâ€“Rashba dominated band structure in an In _{0.75} Ga _{0.25} Asâ€“In _{0.75} Al _{0.25} As device with spin-split carrier densities of $<10^{11}\text{cm}^{-2}$. Journal of Physics Condensed Matter, 2008, 20, 472207.	1.8	12
308	Radio-frequency reflectometry on large gated two-dimensional systems. Review of Scientific Instruments, 2008, 79, 123901.	1.3	12
309	Peaked structure appearing in the field effect mobility of silicon MOS devices at liquid helium temperatures. Journal of Physics C: Solid State Physics, 1974, 7, L353-L355.	1.5	11
310	Title is missing!. Journal of Physics C: Solid State Physics, 1985, 18, L1041-L1047.	1.5	11
311	AbsÃ“nce of valley splitting and quantum interference effects in the quantum hall regime of a narrow two dimensional electron gas in Si. Solid State Communications, 1989, 72, 1065-1069.	1.9	11
312	Lateral transport studies of coupled electron gases. Semiconductor Science and Technology, 1996, 11, 703-711.	2.0	11
313	Effect of finite quantum-well width on the compressibility of a two-dimensional electron gas. Physical Review B, 1997, 55, 6715-6718.	3.2	11
314	Tunnelling transmission resonances through a zero-dimensional structure. Semiconductor Science and Technology, 1997, 12, 875-880.	2.0	11
315	Electronâ€“electron scattering between closely spaced two-dimensional electron gases. Physica B: Condensed Matter, 1998, 249-251, 868-872.	2.7	11
316	Interaction of surface acoustic waves with a narrow electron channel in a piezoelectric material. Physical Review B, 1998, 57, 1654-1663.	3.2	11
317	Schottky gating high mobility Si/Si $1\text{Å}^2 \times \text{Ge}$ x 2D electron systems. Thin Solid Films, 2000, 369, 316-319.	1.8	11
318	Selective breakdown of quantum Hall edge states and non-monotonic Coulomb drag in a GaAsâ€“AlGaAs electronâ€“hole bilayer. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 1693-1696.	2.7	11
319	Direct Observation of Nonequilibrium Spin Population in Quasi-One-Dimensional Nanostructures. Nano Letters, 2010, 10, 2330-2334.	9.1	11
320	Single- and few-electron dynamic quantum dots in a perpendicular magnetic field. Journal of Applied Physics, 2011, 109, .	2.5	11
321	Frequency-dependent magnetoconductance quantisation in 2D systems-a disorder effect. Journal of Physics C: Solid State Physics, 1985, 18, L497-L505.	1.5	10
322	Fabrication and physics of lateral superlattices with 40 nm pitch on high-mobility GaAs GaAlAs heterostructures. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1992, 10, 2904.	1.6	10
323	Anisotropic magnetotransport in two-dimensional electron gases on (311)B GaAs substrates. Journal of Physics Condensed Matter, 1994, 6, 6131-6138.	1.8	10
324	Observation of the effect of electron-electron scattering on the impurity-limited resistivity of a two-dimensional electron gas. Physical Review B, 1995, 51, 13793-13796.	3.2	10

#	ARTICLE	IF	CITATIONS
325	Carrier dynamics and recombination processes of charged excitons in a GaAs/AlGaAs quantum well. <i>Physica B: Condensed Matter</i> , 1999, 272, 412-415.	2.7	10
326	Formation and Recombination Dynamics of Charged Excitons in a GaAs Quantum Well. <i>Physica Status Solidi (B): Basic Research</i> , 2001, 227, 297-306.	1.5	10
327	Interaction correction to the longitudinal conductivity and Hall resistivity in high-quality two-dimensional GaAs electron and hole systems. <i>Physical Review B</i> , 2005, 72, .	3.2	10
328	The 0.7 anomaly in one-dimensional hole quantum wires. <i>Journal of Physics Condensed Matter</i> , 2008, 20, 164205.	1.8	10
329	Quantized acoustoelectric current in an InGaAs quantum well. <i>Journal of Applied Physics</i> , 2008, 103, .	2.5	10
330	Engineering the spin polarization of one-dimensional electrons. <i>Journal of Physics Condensed Matter</i> , 2018, 30, 08LT01.	1.8	10
331	Conductance oscillations and source-drain-limited conduction in Si MOSFETs. <i>Journal of Physics C: Solid State Physics</i> , 1979, 12, L897-L900.	1.5	9
332	A new temperature-dependent magneto-conductance in a disordered electron gas. <i>Journal of Physics C: Solid State Physics</i> , 1985, 18, L383-L392.	1.5	9
333	Transport in GaAs heterojunction ring structures. <i>Superlattices and Microstructures</i> , 1988, 4, 541-544.	3.1	9
334	Differential negative resistance in a one-dimensional mesoscopic system due to single-electron tunnelling. <i>Journal of Physics Condensed Matter</i> , 1990, 2, 2105-2109.	1.8	9
335	Fundamental properties of high mobility InSb—CdTe heterojunctions. <i>Surface Science</i> , 1990, 228, 542-546.	1.9	9
336	Transport properties of closely separated two-dimensional electron gases in a channel-doped back gated high electron mobility transistor. <i>Applied Physics Letters</i> , 1992, 60, 3268-3270.	3.3	9
337	Coulomb blockade in small quantum dots. <i>Scripta Materialia</i> , 1993, 3, 283-291.	0.5	9
338	Transport properties of a wide-quantum-well velocity modulation transistor structure. <i>Semiconductor Science and Technology</i> , 1994, 9, 1744-1747.	2.0	9
339	Weak localization and electron-electron interactions in a two-dimensional grid lateral surface superlattice. <i>Physical Review B</i> , 1994, 49, 8518-8521.	3.2	9
340	One-dimensional ballistic channel with a triple-barrier longitudinal potential: Measurement and model. <i>Physical Review B</i> , 1994, 49, 14078-14080.	3.2	9
341	Variation of the confinement potential of a quasi-one-dimensional electron gas by lateral p-n junctions. <i>Applied Physics Letters</i> , 1996, 68, 1708-1710.	3.3	9
342	Non-equilibrium transport along an edge of variable slope in the fractional quantum Hall regime. <i>Physica B: Condensed Matter</i> , 1998, 249-251, 405-409.	2.7	9

#	ARTICLE	IF	CITATIONS
343	Many-body interactions, the quantum Hall effect, and insulating phases in bilayer two-dimensional hole-gas systems. <i>Physica B: Condensed Matter</i> , 1998, 249-251, 819-823.	2.7	9
344	Electrical properties and uniformity of two dimensional electron gases grown on cleaned SiGe virtual substrates. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1998, 16, 1644.	1.6	9
345	Electron dynamics of a two-dimensional electron gas with a random array of InAs quantum dots. <i>Physical Review B</i> , 1999, 60, 7780-7783.	3.2	9
346	Transport properties of two-dimensional electron gases containing linear ordering InAs self-assembled quantum dots. <i>Applied Physics Letters</i> , 2001, 78, 3896-3898.	3.3	9
347	Coulomb ordering of Anderson-localized electron systems. <i>Europhysics Letters</i> , 2003, 62, 705-711.	2.0	9
348	Gradual decrease of conductance of an adiabatic ballistic constriction below $2e^2/h$. <i>Physical Review B</i> , 2004, 70, .	3.2	9
349	0.7 Analogue structures and exchange interactions in quantum wires. <i>Solid State Communications</i> , 2004, 131, 591-597.	1.9	9
350	Evidence for multiple impurity bands in sodium-doped silicon MOSFETs. <i>Physical Review B</i> , 2006, 73, .	3.2	9
351	Strongly bias-dependent spin injection from Fe into n-type GaAs. <i>Physical Review B</i> , 2007, 75, .	3.2	9
352	Measurement of Coulomb-energy-dependent tunnelling rates in surface-acoustic-wave-defined dynamic quantum dots. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2008, 40, 1136-1138.	2.7	9
353	Spin effects in one-dimensional systems. <i>Journal of Physics Condensed Matter</i> , 2008, 20, 164213.	1.8	9
354	Noncollinear Paramagnetism of a GaAs Two-Dimensional Hole System. <i>Physical Review Letters</i> , 2014, 113, 236401.	7.8	9
355	Anderson localization in silicon inversion layers. <i>CRC Critical Reviews in Solid State Sciences</i> , 1975, 5, 375-384.	1.2	8
356	The radiation hardness of the Si-SiO ₂ interface and carrier localisation in the inversion layer. <i>Journal of Physics C: Solid State Physics</i> , 1977, 10, L445-L450.	1.5	8
357	Electron localisation and the 2D quantised Hall resistance. <i>Journal of Physics C: Solid State Physics</i> , 1982, 15, L861-L870.	1.5	8
358	Quantum corrections to conductivity and energy relaxation in InP and InSb. <i>Physica B: Physics of Condensed Matter & C: Atomic, Molecular and Plasma Physics, Optics</i> , 1983, 117-118, 75-77.	0.9	8
359	Non-metallic transport in silicon inversion layers and the Hall effect. <i>Journal of Physics C: Solid State Physics</i> , 1983, 16, L361-L367.	1.5	8
360	Two-dimensional electron interaction effects in high magnetic fields. <i>Journal of Physics C: Solid State Physics</i> , 1983, 16, L679-L685.	1.5	8

#	ARTICLE	IF	CITATIONS
361	Anisotropic negative magnetoresistance in a variable-thickness electron gas. Journal of Physics C: Solid State Physics, 1985, 18, L1049-L1055.	1.5	8
362	Electron transport across depleted region of a fine-gate GaAs/AlGaAs heterojunction FET. Electronics Letters, 1986, 22, 247.	1.0	8
363	Low-frequency edge magnetoplasmons in the quantum Hall regime under conditions of reduced Coulomb interaction. Journal of Physics Condensed Matter, 1992, 4, 3955-3960.	1.8	8
364	Temperature limits for ballistic quantization in a GaAs/AlGaAs one-dimensional constriction. Journal of Physics Condensed Matter, 1993, 5, L559-L564.	1.8	8
365	Frictional drag between closely spaced two-dimensional electron gases. Surface Science, 1996, 361-362, 134-137.	1.9	8
366	Magnetic field studies of Coulomb drag in a coupled double quantum well system. Semiconductor Science and Technology, 1997, 12, 309-313.	2.0	8
367	Thermopower measurements of semiconductor quantum dots. Physica B: Condensed Matter, 1998, 249-251, 281-285.	2.7	8
368	A simple lateral transport device of strongly interacting electron and hole layers. Applied Physics Letters, 1999, 74, 1603-1605.	3.3	8
369	High-frequency single-electron transport and the quantized acoustoelectric effect. Physica B: Condensed Matter, 2000, 280, 493-494.	2.7	8
370	Effect of temperature and magnetic field on the 0.7 structure in a ballistic one-dimensional wire. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 12, 708-710.	2.7	8
371	Interactions in 2D electron and hole systems in the intermediate and ballistic regimes. Journal of Physics A, 2003, 36, 9249-9262.	1.6	8
372	Unusual conductance collapse in one-dimensional quantum structures. Journal of Physics Condensed Matter, 2004, 16, L279-L286.	1.8	8
373	Benefits of using undoped GaAs/AlGaAs heterostructures: A case study of the zero-bias bias anomaly in quantum wires. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 1200-1204.	2.7	8
374	Disorder and Interaction Effects in Quantum Wires. Journal of Physics: Conference Series, 2012, 376, 012018.	0.4	8
375	Evidence of Novel Quasiparticles in a Strongly Interacting Two-Dimensional Electron System: Giant Thermopower and Metallic Behaviour. Journal of Low Temperature Physics, 2013, 171, 626-631.	1.4	8
376	Quantum ballistic transport in strained epitaxial germanium. Applied Physics Letters, 2017, 111, 233512.	3.3	8
377	Some aspects of localization in two-dimensional systems. Surface Science, 1978, 73, 40-45.	1.9	7
378	Quantum corrections to the Hall effect in III-V semiconductors. Journal of Physics C: Solid State Physics, 1987, 20, 4369-4376.	1.5	7

#	ARTICLE	IF	CITATIONS
379	Low-field magnetotransport in p-type GaAs in the regime of variable-range-hopping conductivity. <i>Physical Review B</i> , 1990, 41, 8572-8575.	3.2	7
380	Enhancement of intersubband transition probability in a one-dimensional constriction. <i>Physical Review B</i> , 1993, 47, 4088-4091.	3.2	7
381	The propagation of low-frequency edge excitations in a two-dimensional electron gas in the IQHE regime. <i>Journal of Physics Condensed Matter</i> , 1995, 7, L435-L443.	1.8	7
382	Equilibrium tunneling between two-dimensional and quasi-one-dimensional electron gases in devices fabricated by in situ focused ion beam lithography. <i>Applied Physics Letters</i> , 1996, 68, 826-828.	3.3	7
383	Quantized Acoustoelectric Current—An Alternative Route Towards a Standard of Electric Current. <i>Journal of Low Temperature Physics</i> , 2000, 118, 555-569.	1.4	7
384	Inter-edge-mode scattering in a high-mobility strained silicon two-dimensional electron system. <i>Journal of Physics Condensed Matter</i> , 2000, 12, 1811-1818.	1.8	7
385	Large transconductance oscillations in a single-well vertical Aharonov-Bohm interferometer. <i>Physical Review B</i> , 2000, 62, R10630-R10632.	3.2	7
386	0.7 Structure in quantum wires observed at crossings of spin-polarised 1D subbands. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2004, 22, 264-267.	2.7	7
387	Examination of multiply reflected surface acoustic waves by observing acoustoelectric current generation under pulse modulation. <i>Physical Review B</i> , 2006, 74, .	3.2	7
388	Activation mechanisms in sodium-doped silicon MOSFETs. <i>Journal of Physics Condensed Matter</i> , 2007, 19, 226216.	1.8	7
389	Tuning the confinement strength in a split-gate quantum wire. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2008, 40, 1645-1647.	2.7	7
390	Patterned backgating using single-sided mask aligners: Application to density-matched electron-hole bilayers. <i>Journal of Applied Physics</i> , 2008, 104, .	2.5	7
391	Effects of inelastic capture, tunneling escape, and quantum confinement on surface acoustic wave-dragged photocurrents in quantum wells. <i>Journal of Applied Physics</i> , 2008, 103, 083714.	2.5	7
392	Coupled double-row formation in a quasi-1D wire. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2010, 42, 1114-1117.	2.7	7
393	Double-row transport in quantum wires of shallow confinement. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2010, 42, 1118-1121.	2.7	7
394	Magnetic focusing with quantum point contacts in the non-equilibrium transport regime. <i>Applied Physics Letters</i> , 2013, 103, .	3.3	7
395	Ballistic injection of electrons in metal-semiconductor junctions. II. Phonon spectroscopy of aluminium. <i>Journal of Physics C: Solid State Physics</i> , 1980, 13, L717-L719.	1.5	6
396	Low-frequency conduction in the gap regions of Landau levels in silicon inversion layers. <i>Surface Science</i> , 1982, 113, 194-198.	1.9	6

#	ARTICLE	IF	CITATIONS
397	Electron localization and the quantized hall resistance in silicon inversion layers. Physica B: Physics of Condensed Matter & C: Atomic, Molecular and Plasma Physics, Optics, 1983, 117-118, 691-693.	0.9	6
398	Quantum transport in narrow Si accumulation layers. Surface Science, 1988, 196, 59-67.	1.9	6
399	Negative magnetoresistance in uniaxially stressed Si(100) inversion layers. Physical Review B, 1988, 38, 1593-1596.	3.2	6
400	Subband occupancies and zero-field spin splitting in InSb-CdTe heterojunctions: magnetotransport experiments and self-consistent calculations. Semiconductor Science and Technology, 1992, 7, 1377-1385.	2.0	6
401	Quantisation of the conductance in units of $e^2/2h$ in a ballistic quasi-one-dimensional channel, produced by strong electric and magnetic fields. Superlattices and Microstructures, 1992, 11, 233-235.	3.1	6
402	Electron conduction characteristics of split-gate structures fabricated on pseudomorphic GaAs-In _x Ga _{1-x} As-AlGaAs heterostructures. Journal of Physics Condensed Matter, 1993, 5, L227-L234.	1.8	6
403	Electron states in double-channel back-gated HEMT structures. Semiconductor Science and Technology, 1993, 8, 123-126.	2.0	6
404	Low temperature operation of Ge δ -Ag ohmic contacts to a high mobility two dimensional electron gas. Journal of Applied Physics, 1993, 74, 5883-5885.	2.5	6
405	Integer quantum Hall states in coupled double electron gas systems at mismatched carrier densities. Journal of Physics Condensed Matter, 1996, 8, L311-L318.	1.8	6
406	Magneto-optical study of excitonic states in 2DEGs near filling factor $\hat{1}/2=1$. Physica B: Condensed Matter, 1998, 249-251, 538-543.	2.7	6
407	A direct measurement of the effects of Fermi energy oscillations in quasi-1D systems. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 6, 518-521.	2.7	6
408	Masking by weak localization of metallic behavior in a two-dimensional electron system in strong parallel magnetic fields. Physical Review B, 2004, 69, .	3.2	6
409	Single-electron transfer between double quantum dots defined by surface acoustic waves. Physica E: Low-Dimensional Systems and Nanostructures, 2006, 34, 546-549.	2.7	6
410	New interaction effects in quantum point contacts at high magnetic fields. Physica E: Low-Dimensional Systems and Nanostructures, 2006, 34, 588-591.	2.7	6
411	Gating schemes for controlling the electron wavefunction between GaAs and In _{0.05} Ga _{0.95} As quasi-one-dimensional channels. Journal of Physics Condensed Matter, 2006, 18, L123-L128.	1.8	6
412	Molecular beam epitaxy of high mobility In _[sub 0.75] Ga _[sub 0.25] As for electron spin transport applications. Journal of Vacuum Science & Technology B, 2009, 27, 2066.	1.3	6
413	Spin-split excitation gap and spin entanglement of a pair of interacting electrons in a quantum dot. Semiconductor Science and Technology, 2009, 24, 115001.	2.0	6
414	Towards the ground state of an electron-hole bilayer. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 1247-1250.	2.7	6

#	ARTICLE	IF	CITATIONS
415	Disorder and electron interaction control in low-doped silicon metal-oxide-semiconductor field effect transistors. Applied Physics Letters, 2010, 97, 142108.	3.3	6
416	Activated and Metallic Conduction in p^+/i^- -Type Modulation-Doped $\text{Ge} - \text{Sn}$ Devices. Physical Review Applied, 2020, 14, .	3.8	6
417	Engineering electron wavefunctions in asymmetrically confined quasi one-dimensional structures. Applied Physics Letters, 2021, 118, .	3.3	6
418	The influence of the electrode on the low temperature annealing of interface states in the Si-SiO ₂ system. Thin Solid Films, 1971, 8, 133-142.	1.8	5
419	Quantum interference and dimensionality in semiconductor structures. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1987, 56, 775-784.	0.6	5
420	Spin-dependent pair generation at Si/SiO ₂ interfaces. Applied Physics Letters, 1988, 53, 1299-1301.	3.3	5
421	Magnetothermopower oscillations in a lateral superlattice. Physical Review B, 1995, 51, 17243-17246.	3.2	5
422	Resonant coupling effects observed in independently contacted triple-quantum-well structures. Journal of Physics Condensed Matter, 1995, 7, L585-L591.	1.8	5
423	Measurements of a composite fermion split-gate. Surface Science, 1996, 361-362, 71-74.	1.9	5
424	Exchange- and correlation-induced charge transfer observed in independently contacted triple-quantum-well structures. Physical Review B, 1996, 53, 15443-15446.	3.2	5
425	Probing the Fermi surfaces of coupled double quantum wells in the presence of an in-plane magnetic field. Journal of Physics Condensed Matter, 1997, 9, 1079-1094.	1.8	5
426	Formation of narrow channels using split back-gates defined by in situ focused ion beam lithography. Semiconductor Science and Technology, 1997, 12, 137-139.	2.0	5
427	Thermopower of one-dimensional devices – measurement and applications. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 6, 534-537.	2.7	5
428	Optical control of the mobility of a MODFET with a layer of self-assembled quantum dots. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 7, 479-483.	2.7	5
429	Quantised current driven by surface acoustic waves. Materials Science and Engineering C, 2001, 15, 97-100.	7.3	5
430	Ballistic electron spectroscopy. Applied Physics Letters, 2006, 89, 212103.	3.3	5
431	Direct observation of spin polarization in GaAs quantum wires by transverse electron focusing. Journal of Physics: Conference Series, 2018, 964, 012002.	0.4	5
432	Formation of a non-magnetic, odd-denominator fractional quantized conductance in a quasi-one-dimensional electron system. Applied Physics Letters, 2019, 115, 123104.	3.3	5

#	ARTICLE	IF	CITATIONS
433	Conductance oscillations in two-dimensional transport. Surface Science, 1980, 98, 218-219.	1.9	4
434	Intrinsic stress in narrow silicon metal-oxide-semiconductor field-effect transistors: Magnetotransport measurements. Applied Physics Letters, 1988, 53, 198-200.	3.3	4
435	Room temperature negative differential resistance in the quasi-one-dimensional ballistic resistor. Electronics Letters, 1990, 26, 171.	1.0	4
436	One-dimensional ballistic transport of electrons. Semiconductor Science and Technology, 1990, 5, 1185-1188.	2.0	4
437	Transmission coefficients and Hall resistance in a small cross-shaped semiconductor junction. Journal of Physics Condensed Matter, 1991, 3, 1961-1965.	1.8	4
438	Negative magnetoresistance in a parallel-conducting InGaAs structure. Journal of Physics Condensed Matter, 1992, 4, L487-L494.	1.8	4
439	Quasi-one-dimensional transport in semiconductor microstructures. Physica Scripta, 1992, T45, 200-205.	2.5	4
440	Observations of plasmons and edge magnetoplasmons in voltage-tunable dots in GaAs/AlGaAs heterostructures. Journal of Physics Condensed Matter, 1993, 5, 1517-1524.	1.8	4
441	Detecting charge redistribution between edge states in a quantum dot. Journal of Physics Condensed Matter, 1994, 6, L273-L278.	1.8	4
442	Low temperature magneto-photoluminescence investigations of the 2D hole system in p-type GaAs-AlGaAs heterojunctions. Physica B: Condensed Matter, 1994, 201, 397-402.	2.7	4
443	Evidence of quantum lateral confinement in side-gated resonant tunnelling diodes formed by patterned substrate regrowth. Applied Physics Letters, 1996, 68, 1702-1704.	3.3	4
444	Ballistic composite fermions in semiconductor nanostructures. Physical Review B, 1996, 53, 9602-9605.	3.2	4
445	Negative transconductance in parallel conducting systems controlled by device geometry and magnetic field. Semiconductor Science and Technology, 1996, 11, 483-488.	2.0	4
446	Mobility ($106 \text{ cm}^2 \text{ V}^{-1} \text{ s}^{-1}$) of 2DEGs, 30 nm from ex situ patterned GaAs regrowth interfaces. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1998, 51, 202-206.	3.5	4
447	Nonlinear interaction between surface acoustic waves and electrons in GaAs resonant-tunneling structures. Physical Review B, 2000, 62, 6948-6951.	3.2	4
448	Fermi-Liquid Behaviour near the Crossover from 'Metal' to 'Insulator' in 2D Systems. Physica Status Solidi (B): Basic Research, 2002, 230, 89-95.	1.5	4
449	Interactions in high-mobility 2D electron and hole systems. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 22, 218-223.	2.7	4
450	Photon-induced conductance steps and in situ modulation of disorder in mesoscopic electron systems. Physical Review B, 2004, 70, .	3.2	4

#	ARTICLE	IF	CITATIONS
451	Single-photon detection mechanism in a quantum dot transistor. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2005, 26, 356-360.	2.7	4
452	Collapse of nonequilibrium charge states in an isolated quantum dot using surface acoustic waves. <i>Physical Review B</i> , 2007, 75, .	3.2	4
453	Magnetotransconductivity of Hubbard bands induced in silicon MOSFETs. <i>Physica B: Condensed Matter</i> , 2007, 400, 218-223.	2.7	4
454	Investigation of single-electron dynamics in tunnelling between zero- and one-dimensional states. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2008, 40, 1017-1021.	2.7	4
455	Interactions and non-magnetic fractional quantization in one-dimension. <i>Applied Physics Letters</i> , 2021, 119, 110502.	3.3	4
456	The influence of oxygen annealing on ion drift in SiO ₂ . <i>Physica Status Solidi A</i> , 1973, 18, K19-K22.	1.7	3
457	Ballistic electron transport in quasi-one-dimensional systems. <i>Surface Science</i> , 1990, 229, 233-238.	1.9	3
458	Magnetotransport in high mobility InSb—CdTe heterojunctions: Electric spin-splitting of subbands and high pressure effects. <i>Superlattices and Microstructures</i> , 1991, 9, 51-54.	3.1	3
459	The physics of the two-dimensional electron gas base vertical hot electron transistor. <i>Semiconductor Science and Technology</i> , 1992, 7, B536-B539.	2.0	3
460	The growth and physical properties of high quality pseudomorphic In _x Ga _{1-x} As HEMT structures. <i>Journal of Crystal Growth</i> , 1993, 127, 601-605.	1.5	3
461	Transport by single and few electrons in GaAs mesoscopic structures. <i>Physica A: Statistical Mechanics and Its Applications</i> , 1993, 200, 65-79.	2.6	3
462	Design considerations for channel-doped back-gated high electron mobility structures. <i>Applied Physics Letters</i> , 1993, 62, 1274-1276.	3.3	3
463	Far-infrared study of a quasi-one-dimensional electron gas formed by molecular beam epitaxial regrowth on patterned GaAs. <i>Applied Physics Letters</i> , 1994, 64, 3296-3298.	3.3	3
464	Reflection of edge states in the fractional quantum Hall regime. <i>Solid State Communications</i> , 1995, 96, 327-331.	1.9	3
465	Temperature studies of the tunnelling between parallel two-dimensional electron gases. <i>Solid-State Electronics</i> , 1996, 40, 413-415.	1.4	3
466	Experimental evidence of a metal-insulator transition in a half-filled Landau level. <i>Solid State Communications</i> , 1997, 102, 327-330.	1.9	3
467	Hydrogen radical cleaning and low energy electron stimulated desorption of surface contaminants for MBE regrowth of GaAs. <i>Applied Surface Science</i> , 1998, 123-124, 308-312.	6.1	3
468	Excitons, spin-waves and Skyrmions in the optical spectra of a two dimensional electron gas. <i>Solid-State Electronics</i> , 1998, 42, 1169-1174.	1.4	3

#	ARTICLE	IF	CITATIONS
469	Stark effect of negatively and positively charged excitons in semiconductor quantum wells. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 1998, 2, 87-92.	2.7	3
470	Plasmons in spatially non-uniform magnetic fields. <i>Physica B: Condensed Matter</i> , 1998, 249-251, 286-290.	2.7	3
471	Ultrashort FETs formed by GaAs/AlGaAs MBE regrowth on a patterned $\bar{\Gamma}$ -doped GaAs layer. <i>Journal of Crystal Growth</i> , 1999, 201-202, 761-764.	1.5	3
472	Si/SiGe n-type inverted modulation doping using ion implantation. <i>Thin Solid Films</i> , 2000, 369, 324-327.	1.8	3
473	Evidence for charging effects in an open dot at zero magnetic field. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2000, 6, 418-422.	2.7	3
474	Metallic behaviour and localisation in 2D GaAs hole systems. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2001, 11, 161-166.	2.7	3
475	Experimental evidence for screening effects from surface states in GaAs/AlGaAs based nanostructures. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2004, 22, 570-573.	2.7	3
476	Electron pumping through quantum dots defined in parallel etched quantum wires. <i>Microelectronics Journal</i> , 2008, 39, 365-368.	2.0	3
477	Conductance oscillations in two-dimensional GaAs impurity bands. <i>The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties</i> , 1980, 42, 947-947.	0.6	2
478	Two-dimensional conductivity in the contact regions of silicon MOSFETs. <i>Journal of Physics C: Solid State Physics</i> , 1980, 13, L619-L622.	1.5	2
479	Non-linearities and electron-plasmon coupling in metal-semiconductor point contacts. <i>Journal of Physics C: Solid State Physics</i> , 1985, 18, L87-L92.	1.5	2
480	The metal-insulator transition in n-type $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$. <i>Journal of Physics Condensed Matter</i> , 1989, 1, 4805-4815.	1.8	2
481	Temperature dependence of the conductivity in uniaxially stressed Si inversion layers at low temperatures. <i>Solid State Communications</i> , 1989, 70, 793-796.	1.9	2
482	Fine structure in the I - V characteristics of GaAs/AlGaAs submicron diameter triple barrier diodes. <i>Surface Science</i> , 1992, 267, 388-391.	1.9	2
483	Magneto-optics and magneto-capacitance studies of voltage-tuneable GaAs/AlGaAs quantum dots. <i>Journal of Physics Condensed Matter</i> , 1993, 5, L1-L8.	1.8	2
484	Double two-dimensional electron gas structure formed by molecular beam epitaxy regrowth on an epitaxially patterned GaAs back gate. <i>Applied Physics Letters</i> , 1994, 65, 1943-1945.	3.3	2
485	A non-invasive voltage probe to measure Coulomb charging. <i>Surface Science</i> , 1994, 305, 553-557.	1.9	2
486	One-dimensional wire formed by molecular-beam epitaxial regrowth on a patterned pnpnp GaAs substrate. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1994, 12, 1277.	1.6	2

#	ARTICLE	IF	CITATIONS
487	Tunnelling between two-dimensional electron gases up to 25 T. <i>Physica B: Condensed Matter</i> , 1995, 211, 430-432.	2.7	2
488	The growth of high mobility heterostructures on (311)B GaAs. <i>Microelectronics Journal</i> , 1995, 26, 897-902.	2.0	2
489	Tuneable confinement energies in a quasi-one-dimensional electron gas regrown on a patterned GaAs backgate. <i>Solid State Communications</i> , 1995, 96, 85-88.	1.9	2
490	Magneto-optical probe of the two-dimensional hole-system low-temperature ground states. <i>Physical Review B</i> , 1995, 51, 7357-7360.	3.2	2
491	Coulomb blockade as a non-invasive probe in double layer 2DEG systems. <i>Surface Science</i> , 1996, 361-362, 154-157.	1.9	2
492	Electron transport in a non-planar 2DEG. <i>Surface Science</i> , 1996, 361-362, 587-590.	1.9	2
493	Detection of the oscillation of the Fermi energy of a 2DEG. <i>Surface Science</i> , 1996, 361-362, 608-612.	1.9	2
494	Evolution of GaAs quantum well excitons with excess electron density and magnetic field. <i>Solid-State Electronics</i> , 1996, 40, 275-280.	1.4	2
495	Quantum magnetotransport properties of short quantum wires. <i>Physical Review B</i> , 1997, 56, 6758-6763.	3.2	2
496	Back gating of a two-dimensional hole gas in a SiGe quantum well. <i>Applied Physics Letters</i> , 1997, 70, 1870-1872.	3.3	2
497	The investigation of 1D and 2D phenomena using double-layer electron systems. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 1998, 3, 52-57.	2.7	2
498	Onset of subband locking in double-quantum-well structures as the signature of wave function delocalization. <i>Physica B: Condensed Matter</i> , 1998, 249-251, 850-854.	2.7	2
499	Bonding and antibonding states in strongly coupled ballistic one-dimensional wires. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2000, 6, 581-585.	2.7	2
500	Desorption of organic species from the GaAs (100) surface at low temperatures using low energy electron irradiation in a hydrogen ambient. <i>Applied Physics Letters</i> , 2000, 76, 3034-3036.	3.3	2
501	Quantum dot with independently tunable tunneling barriers fabricated using an atomic force microscope. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2002, 20, 2810.	1.6	2
502	Localisation in Strongly Interacting 2D GaAs Systems. <i>Physica Status Solidi (B): Basic Research</i> , 2002, 230, 81-87.	1.5	2
503	Exchange-driven bilayer-to-monolayer charge transfer in an asymmetric double-quantum-well. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2002, 12, 304-306.	2.7	2
504	Non-invasive detection of the ionic and covalent charge states of an isolated double dot system. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2004, 22, 522-525.	2.7	2

#	ARTICLE	IF	CITATIONS
505	Ballistic transport in one-dimensional bilayer hole systems. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2006, 34, 550-552.	2.7	2
506	Field-tunable magnetic phases in a semiconductor-based two-dimensional Kondo lattice. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2008, 40, 942-948.	2.7	2
507	Anticrossing of Spin-Split Subbands in Quasi-One-Dimensional Wires. <i>Physical Review Letters</i> , 2008, 100, 226804.	7.8	2
508	MBE growth and patterned backgating of electron-hole bilayer structures. <i>Journal of Crystal Growth</i> , 2009, 311, 1988-1993.	1.5	2
509	Tunneling of hybridized pairs of electrons through a one-dimensional channel. <i>Advances in Physics: X</i> , 2017, 2, 545-568.	4.1	2
510	Hall resistance anomalies in the integer and fractional quantum Hall regime. <i>Physical Review B</i> , 2020, 102, .	3.2	2
511	Influence of Inversion Symmetry on the Metallic Behaviour in a Dilute Two-dimensional Hole System. <i>Australian Journal of Physics</i> , 2000, 53, 523.	0.6	2
512	Enhanced coherent terahertz emission from indium arsenide. <i>Journal of Modern Optics</i> , 2000, 47, 1847-1856.	1.3	2
513	Single-electron pump with highly controllable plateaus. <i>Applied Physics Letters</i> , 2021, 119, .	3.3	2
514	Effects of biased and unbiased illuminations on two-dimensional electron gases in dopant-free GaAs/AlGaAs. <i>Physical Review B</i> , 2022, 105, .	3.2	2
515	Universality of conductance oscillations in GaAs FETs. <i>Journal of Physics C: Solid State Physics</i> , 1984, 17, L985-L989.	1.5	1
516	Parallel magnetoresistance and phase relaxation length and the three-dimensional to two-dimensional transition of electronic transport in a GaAs MESFET. <i>Surface Science</i> , 1986, 170, 701-707.	1.9	1
517	Experimental determination of large intrinsic edge stresses in narrow silicon structures. <i>Semiconductor Science and Technology</i> , 1989, 4, 1080-1083.	2.0	1
518	Physics and fabrication of one-dimensional sub-micron semiconducting channels. <i>Microelectronic Engineering</i> , 1989, 9, 369-372.	2.4	1
519	Electronic transport in ballistic structures. <i>Microelectronic Engineering</i> , 1990, 11, 35-38.	2.4	1
520	The fabrication of submicron gated wires on GaAs/AlGaAs heterostructures using low energy Ga ion beam damage. <i>Microelectronic Engineering</i> , 1990, 11, 19-22.	2.4	1
521	Quantum interference and Landau level broadening in narrow GaAs-AlGaAs channels. <i>Journal of Physics Condensed Matter</i> , 1991, 3, 1003-1010.	1.8	1
522	Magneto-optical spectroscopy of neutral and negatively charged excitons in GaAs quantum wells. <i>Surface Science</i> , 1996, 361-362, 451-455.	1.9	1

#	ARTICLE	IF	CITATIONS
523	Far-infrared study of a laterally confined electron gas formed by molecular beam epitaxial regrowth on a patterned (100) n+-GaAs substrate. Applied Physics Letters, 1997, 71, 497-499.	3.3	1
524	The physics and fabrication of in situ back-gated (311)A hole gas heterojunctions. Microelectronics Journal, 1997, 28, 795-801.	2.0	1
525	Electron coupling effects on negatively charged excitons in GaAs double quantum wells. Solid-State Electronics, 1998, 42, 1569-1574.	1.4	1
526	Multiple subband crossing in a one-dimensional hole gas with enhanced g-factors. Physica B: Condensed Matter, 1998, 249-251, 166-170.	2.7	1
527	Experimental determination of spectral densities in quasi-one-dimensional electron systems. Physica B: Condensed Matter, 1998, 249-251, 175-179.	2.7	1
528	One-dimensional electron transport in devices fabricated by MBE regrowth over a patterned δ -doped backgate. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 6, 526-529.	2.7	1
529	Novel effects produced on a two dimensional electron gas by introducing InAs dots in the plane of the quantum well. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 6, 276-279.	2.7	1
530	Simulation of surface field THz generation in a magnetic field. , 2001, , .		1
531	Dynamic of Spin Triplet and Singlet Trions in a GaAs Quantum Well. Physica Status Solidi A, 2002, 190, 809-812.	1.7	1
532	Experimental studies of composite fermion conductivity: dependence on carrier density. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 12, 105-108.	2.7	1
533	Investigation of the zero-field 2D δ -metallic state with r_s and $k_F l$ controlled independently. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 12, 616-619.	2.7	1
534	Measurements of composite fermion conductivity dependence on carrier density. Journal of Physics Condensed Matter, 2004, 16, 1095-1101.	1.8	1
535	Stability of the bilayer $\nu=1$ quantum Hall state under charge imbalance. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 22, 40-43.	2.7	1
536	Jain's Kivelson-type resonance as a noninvasive probe of screening in the quantum Hall regime. Microelectronics Journal, 2005, 36, 425-427.	2.0	1
537	Interaction effects in high-mobility two-dimensional electron and hole systems. Physica Status Solidi (B): Basic Research, 2005, 242, 1204-1208.	1.5	1
538	Suppression of spin-splitting in $\text{Al}_{0.33}\text{Ga}_{0.67}\text{As}/\text{Al}_x\text{Ga}_{1-x}\text{As}$ heterostructures with x varying from 0.10 to 0.15. Semiconductor Science and Technology, 2007, 22, 722-727.	2.0	1
539	Spontaneous spin polarisation in one dimension under finite DC-bias. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 1295-1297.	2.7	1
540	Sensitivity of the magnetic state of a spin lattice on itinerant electron orbital phase. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 1460-1463.	2.7	1

#	ARTICLE	IF	CITATIONS
541	Electron population control of a highly isolated quantum dot using surface-acoustic waves. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 1596-1598.	2.7	1
542	Screening long-range Coulomb interactions in 2D hole systems using a bilayer heterostructure. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 1700-1702.	2.7	1
543	Variation of the hopping exponent in disordered silicon MOSFETs. Journal of Physics Condensed Matter, 2008, 20, 415226.	1.8	1
544	Magnetic-field-induced instabilities in localized two-dimensional electron systems. Physical Review B, 2008, 78, .	3.2	1
545	Quantum transport in one-dimensional GaAs hole systems. International Journal of Nanotechnology, 2008, 5, 318.	0.2	1
546	Radio-frequency reflectometry—A fast and sensitive measurement method for two-dimensional systems. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 1192-1195.	2.7	1
547	Effect of low transverse magnetic field on the confinement strength in a quasi-1D wire. , 2013, , .		1
548	Early work on semiconductor quantum nanoelectronics in the Cavendish Laboratory. Journal of Physics Condensed Matter, 2016, 28, 421003.	1.8	1
549	Conductance quantisation in patterned gate In _{0.75} Ga _{0.25} As structures up to 6 $\times 10^4$ \AA — \AA ($2e^2/h$). Journal of Physics Condensed Matter, 2019, 31, 104002.	1.8	1
550	Length Scales and the Quantised Hall Effect. , 1985, , 279-282.		1
551	Conductance in Quantum Boxes: Interference and Single Electron Effects. NATO ASI Series Series B: Physics, 1995, , 201-216.	0.2	1
552	THE Si-SiO ₂ INTERFACE AND LOCALIZATION IN THE INVERSION LAYER. , 1978, , 407-411.		0
553	Localization and interaction effects in a two dimensional electron gas. Lecture Notes in Physics, 1981, , 177-190.	0.7	0
554	Magnetophonon effect in GaAs Schottky gate field-effect transistors. Applied Physics Letters, 1988, 53, 54-56.	3.3	0
555	A novel field-effect mobility measurement on a gateless InGaAs/InAlAs heterojunction in a parallel magnetic field. Journal of Applied Physics, 1989, 66, 4560-4561.	2.5	0
556	Electron magnetotransport in uniaxially stressed Si(100) inversion layers. Semiconductor Science and Technology, 1989, 4, 828-830.	2.0	0
557	The Growth and Physics of MBE Structures. Physica Scripta, 1989, T29, 141-146.	2.5	0
558	One dimensional ballistic transport in GaAs microstructures. Microelectronic Engineering, 1990, 11, 3-9.	2.4	0

#	ARTICLE	IF	CITATIONS
559	One-dimensional transport phenomena in GaAs heterojunction structures. Physica A: Statistical Mechanics and Its Applications, 1990, 168, 112-120.	2.6	0
560	Coupling between localized states in resonant tunnelling. Journal of Physics Condensed Matter, 1991, 3, 5207-5211.	1.8	0
561	Side-gated double barrier resonant tunnelling diodes formed by patterned substrate regrowth. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1995, 35, 198-202.	3.5	0
562	A hole facet wire formed by MBE regrowth over an ex-situ patterned GaAs substrate. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1995, 35, 203-207.	3.5	0
563	Universal dissipative resistivity in the fractional quantum Hall effect of two-dimensional hole systems. Physical Review B, 1995, 52, R5507-R5510.	3.2	0
564	Electron beam induced damage of silicon germanium. Microelectronic Engineering, 1997, 35, 59-62.	2.4	0
565	Far-infrared study of a quasi-one-dimensional electron gas formed on (100) GaAs with hole gas sidegates on a (311)A GaAs substrate. Microelectronic Engineering, 1998, 43-44, 431-436.	2.4	0
566	Experimental studies of T-shaped quantum dot transistors: Phase-coherent electron transport. Solid State Communications, 1998, 105, 109-111.	1.9	0
567	Experimental evidence for a metal-insulator transition and geometric effect in a half-filled Landau level. Physica E: Low-Dimensional Systems and Nanostructures, 1998, 2, 78-81.	2.7	0
568	Charged excitons under applied electric and magnetic fields. Physica B: Condensed Matter, 1998, 249-251, 584-588.	2.7	0
569	Selective area oxide desorption by electron irradiation in a H ₂ ambient on GaAs (100). Applied Physics Letters, 1999, 74, 950-952.	3.3	0
570	Low-dimensional devices fabricated by molecular beam epitaxy regrowth over patterned δ -doped backgates. Microelectronics Journal, 1999, 30, 315-318.	2.0	0
571	Anomalous integer quantum Hall states in coupled double quantum wells and the effect of Landau level broadening. Journal of Physics Condensed Matter, 1999, 11, 3711-3728.	1.8	0
572	Far-infrared spectroscopy of a two-dimensional electron gas in a tunable, periodically modulated magnetic field. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 6, 738-741.	2.7	0
573	Single electron transport in samples containing InAs self-assembled dashes and dots. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 6, 486-489.	2.7	0
574	Inverted modulation-doped n-type Si/Si _{0.77} Ge _{0.23} heterostructures. Microelectronic Engineering, 2000, 53, 205-208.	2.4	0
575	Enhanced coherent THz emission from [100] GaAs in the presence of a magnetic field. , 2000, , .		0
576	Wigner-like crystallization of Anderson-localized electron systems with low electron densities. Low Temperature Physics, 2002, 28, 930-934.	0.6	0

#	ARTICLE	IF	CITATIONS
577	Spin-dependent transport in a two-dimensional GaAs electron gas in a parallel magnetic field. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 12, 412-415.	2.7	0
578	Fermi-liquid behaviour near the crossover from "metal" to "insulator" of 2D electron and hole systems. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 12, 595-599.	2.7	0
579	DEVIATION FROM EXACT CONDUCTANCE QUANTIZATION IN A SHORT CLEAN ONE-DIMENSIONAL CHANNEL. International Journal of Nanoscience, 2003, 02, 551-558.	0.7	0
580	Can the conductance step of a single-mode ballistic constriction be lower than $2e^2/h$?. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 22, 268-271.	2.7	0
581	Leakage current induced anomalies in the photoluminescence of GaAs coupled quantum wells. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 612-615.	0.8	0
582	Evidence for a finite compressibility of a quasi-one-dimensional ballistic channel. Microelectronics Journal, 2005, 36, 331-333.	2.0	0
583	Closely spaced, independently contacted electron-hole bilayers in GaAs-AlGaAs heterostructures. Physica E: Low-Dimensional Systems and Nanostructures, 2006, 34, 689-692.	2.7	0
584	Comparison of vibrational spectroscopy techniques to investigate the dehydration behaviour of piroxicam monohydrate from compacts. European Journal of Pharmaceutical Sciences, 2007, 32, S9.	4.0	0
585	0.7 Structure and zero bias anomaly in one-dimensional hole systems. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 1501-1503.	2.7	0
586	Metallic behavior in low-disorder two-dimensional hole systems in the presence of long- and short-range disorder. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 1599-1601.	2.7	0
587	Uniformity of electron pumping regime in two GaAs tunable-barrier pumps. , 2008, , .		0
588	Effect of a perpendicular magnetic field on the zero-bias anomaly in two-dimensional electron systems. Physical Review B, 2008, 78, .	3.2	0
589	Characterisation of spin-incoherent transport in one dimension. Journal of Physics: Conference Series, 2009, 150, 032029.	0.4	0
590	Non-invasive charge detection in surface-acoustic-wave-defined dynamic quantum dots. Applied Physics Letters, 2016, 109, 183501.	3.3	0
591	Cavity assisted spin reconfiguration in a quantum wire. Journal of Physics: Conference Series, 2018, 964, 012003.	0.4	0
592	Advances in interaction effects in the quasi one-dimensional electron gas. Frontiers of Nanoscience, 2021, 20, 7-29.	0.6	0
593	Is there a true metallic state in two dimensions?. Springer Proceedings in Physics, 2001, , 735-738.	0.2	0
594	Rapid recombination process of free trions. Springer Proceedings in Physics, 2001, , 497-498.	0.2	0

#	ARTICLE	IF	CITATIONS
595	Excess carrier effects upon the excitonic absorption thresholds of remotely doped GaAs/AlGaAs quantum wells. Springer Proceedings in Physics, 2001, , 505-506.	0.2	0
596	Magnetic field enhanced terahertz emission from semiconductor surfaces. Springer Proceedings in Physics, 2001, , 178-179.	0.2	0
597	Localisation and Interaction Effects in the 2D Electron Gas of the Silicon Inversion Layer. , 1984, , 681-686.		0
598	Electrons and Phonons in One and Two Dimensions in Semiconductor Structures. Springer Series in Surface Sciences, 1985, , 176-195.	0.3	0
599	Thermopower in Silicon Inversion Layers. , 1985, , 429-432.		0
600	Aspects of 2D And 3D Conduction in Doped Semiconductors. , 1985, , 459-476.		0
601	One-Dimensional Localisation Beyond First Order in Narrow Silicon Mosfets. , 1985, , 425-428.		0
602	2D Localisation and Interaction Effects in Semiconductor Structures. Springer Proceedings in Physics, 1986, , 323-330.	0.2	0
603	Transport Properties of Narrow, Variable Width Channels in the 2DEG of a GaAs:AlGaAs Heterojunction. Springer Series in Solid-state Sciences, 1988, , 208-217.	0.3	0
604	Ballistic Transport in Quasi-One-Dimensional Structures. NATO ASI Series Series B: Physics, 1989, , 115-141.	0.2	0
605	New Method for High-Accuracy Determination of the Fine-Structure Constant Based on Quantized Hall Resistance. Perspectives in Condensed Matter Physics, 1989, , 145-148.	0.1	0
606	Quantum Interference in Semiconductor Devices. NATO ASI Series Series B: Physics, 1989, , 137-147.	0.2	0
607	Quantisation of Resistance in One-Dimensional Ballistic Transport. Springer Series in Solid-state Sciences, 1989, , 366-370.	0.3	0
608	Ballistic Electronic Transport in Semiconductor Structures. , 1990, , 251-259.		0
609	Ballistic Electronic Transport in GaAs-AlGaAs Heterojunctions. NATO ASI Series Series B: Physics, 1990, , 431-434.	0.2	0
610	Controllable Scattering, Fabry-Pérot States and Quantum Coupling in Ballistic Devices. Springer Series in Solid-state Sciences, 1990, , 88-98.	0.3	0
611	Aspects of One Dimensional Transport Effects in Gallium Arsenide Heterojunction Structures. NATO ASI Series Series B: Physics, 1991, , 451-467.	0.2	0
612	Quantum Interference and Magneto-Resistance in Gallium Arsenide Structures. Physics and Chemistry of Materials With Low-dimensional Structures, 1992, , 137-153.	1.0	0

#	ARTICLE	IF	CITATIONS
613	Far-Infrared Transmission of Voltage-Tunable GaAs-(Ga,Al)As Quantum Dots in High Magnetic Fields. Springer Series in Solid-state Sciences, 1992, , 339-343.	0.3	0
614	Phase transitions in high magnetic fields. Lecture Notes in Physics, 1983, , 479-487.	0.7	0
615	Interactions in High-Mobility 2D Electron and Hole Systems. , 2004, , 349-370.		0